
Current induced regeneration CIR of BO-LID prone silicon solar cells for mass production

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Why is Light-Induced Degradation (LID) important?



**Germany's largest solar park- 166 MW
(in Meuro and Schipkau)**



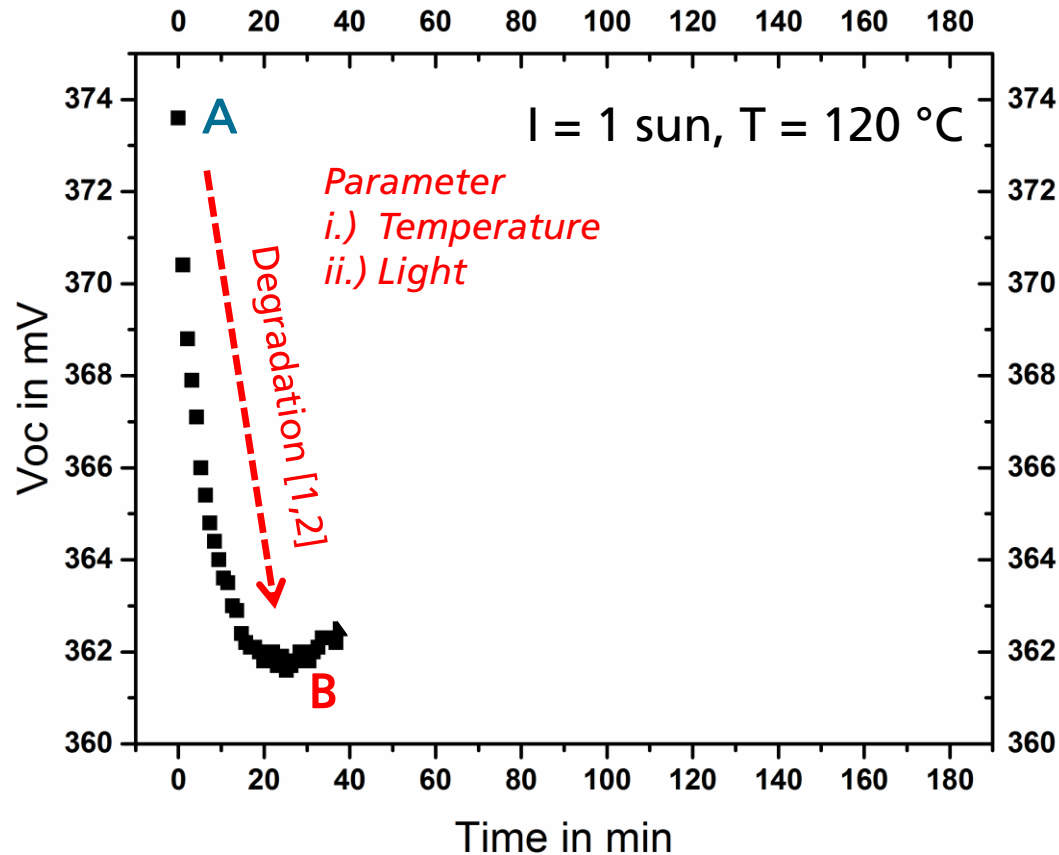
**Taiwan's largest solar rooftop power plant
(in Tainan)**

- Detrimental loss of efficiency (3 - 20 %, relative)
- For 200 MW Fab → ~ 6 MW loss due to LID (3 %) → ~\$2.28 Mio per year (\$ 0.38/Watt)
→ 0.6 MW loss reduction due to LID control (0.3 %) → \$ 0.23 Mio per year

LID threatens business case of solar parks → Important to prevent or control LID effect!

Overcoming LID

Degradation - Regeneration - Cycle



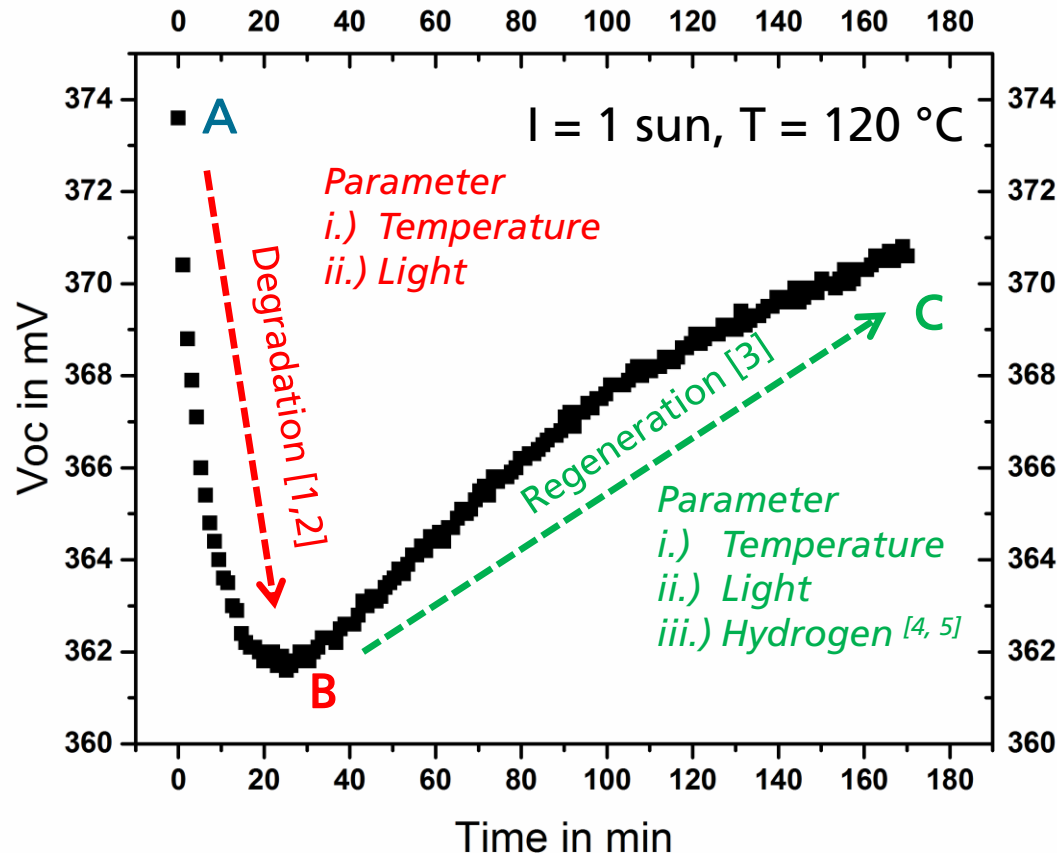
■ Light induced degradation
LID: Reducing τ of Si-bulk
during operation

Transient degradation-regeneration cycle of a Cz mono Si cell

- 3 [1] Schmidt, J et. al., 3rd World Conference on Photovoltaic Energy Conversion, Osaka, Japan, (2003)
 [2] V. V. Voronkov and R. Falster Journal of Applied Physics 107, 053509 (2010);
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 [4] Münzer, K.A. 24th European PVSEC, Hamburg, Germany, (2009)
 [5] Wilking, S. et. al., *J. Appl. Phys.* 113 (19), S. 194503, (2013)

Overcoming LID

Degradation - Regeneration - Cycle



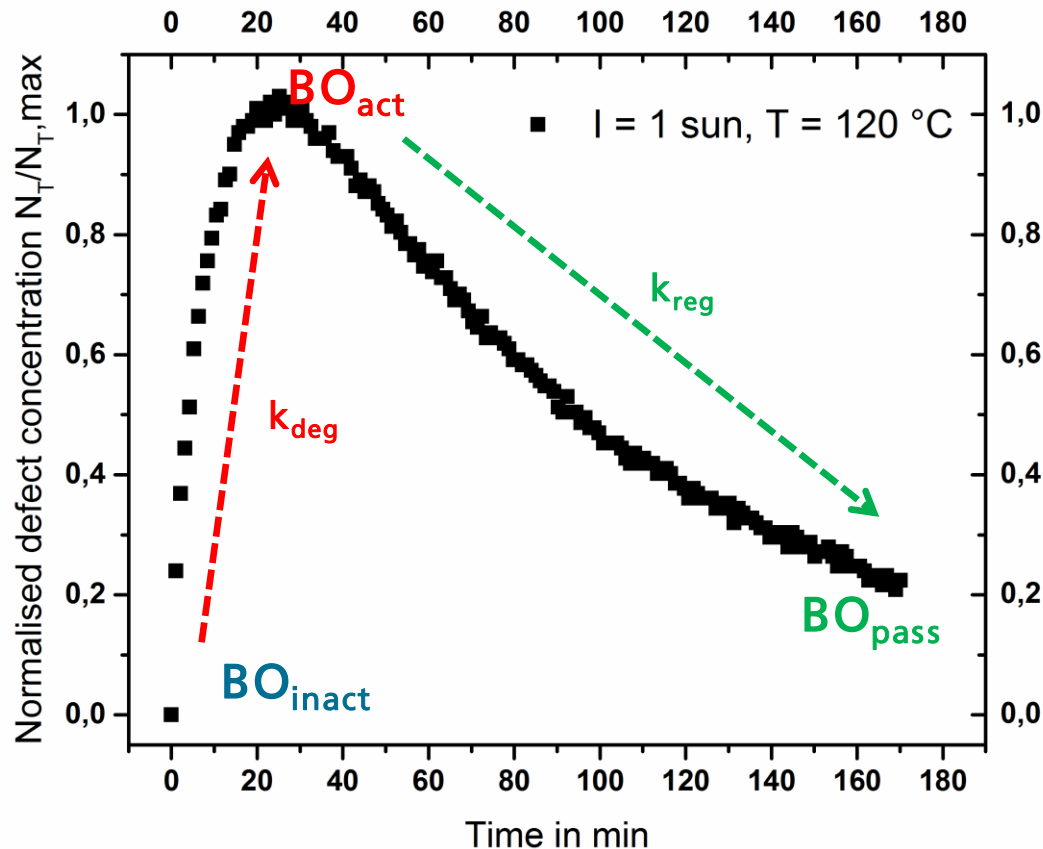
- Light induced degradation LID: Reducing τ of Si-bulk during operation
- Solution: Regeneration process for longterm passivation of defects

Transient degradation-regeneration cycle of a Cz mono Si cell

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Overcoming LID

Degradation - Regeneration - Cycle



Normalised defect concentration of a transient degradation-regeneration cycle of a Cz mono Si cell

Consecutive reaction:

i.) Degradation:



ii.) Regeneration:



For fast process:

Increase k_{deg} and k_{reg}

Influence of
temperature and
injection on reaction
velocities?

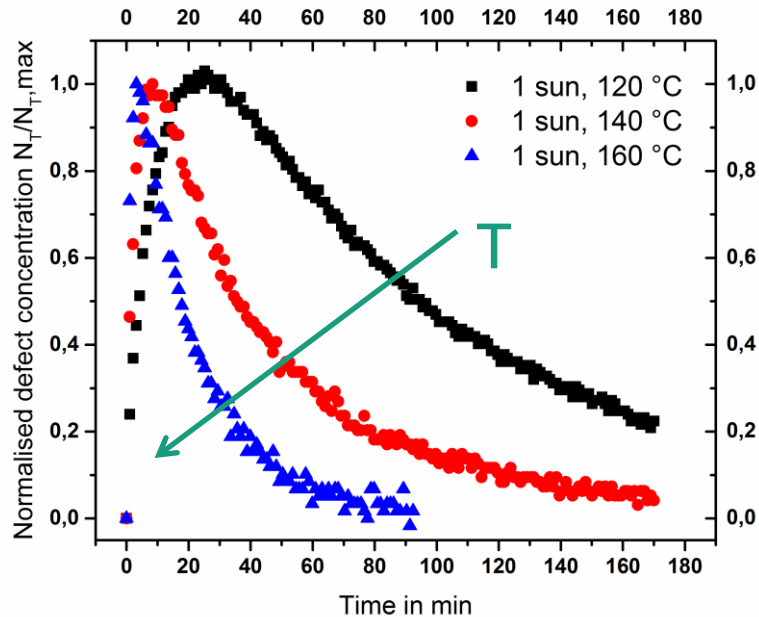
Content

- Accelerating the degradation - regeneration - cycle
- Current induced regeneration CIR
 - Comparison of LIR and CIR
 - Implementing CIR in the value chain
- Application of CIR on cell and module level
 - Simulations
 - Proof of concept
- Summary

Accelerating the degradation - regeneration - cycle

Influence of temperature and illumination

Temperature



Transient degradation-regeneration cycle of neighboured Cz mono Si cells in dependence on temperature

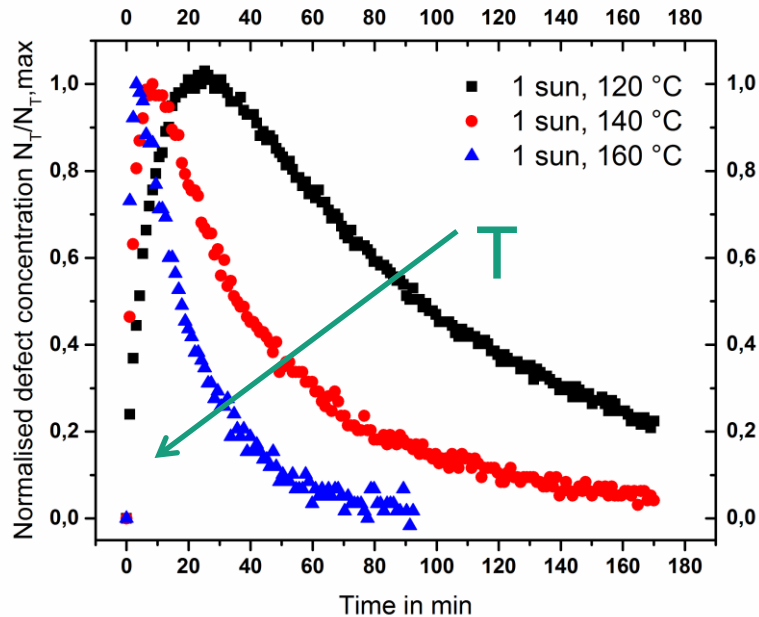
Exponential increase with T:

$$k_i = v_{ch,i} * \exp(-E_{A,i}/kT)$$

Accelerating the degradation - regeneration - cycle

Influence of temperature and illumination

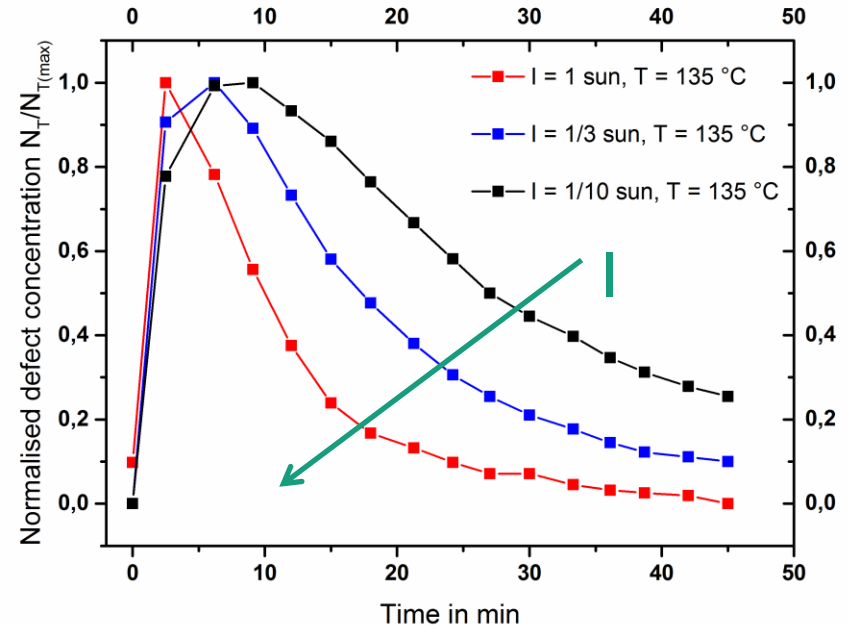
Temperature



Transient degradation-regeneration cycle of neighboured Cz mono Si cells in dependence on temperature

Exponential increase with T:
 $k_i = v_{ch,i} \cdot \exp(-E_{A,i}/kT)$

Intensity



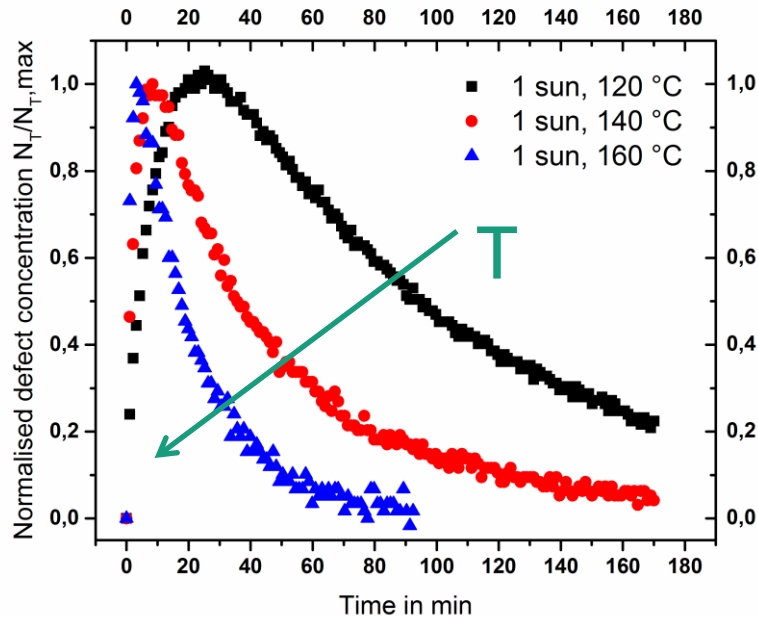
Transient degradation-regeneration cycle of Cz mono Si cell in dependence on light intensity (Data taken from [3])

Linear increase of k_{reg} with I

Accelerating the degradation - regeneration - cycle

Influence of temperature and illumination

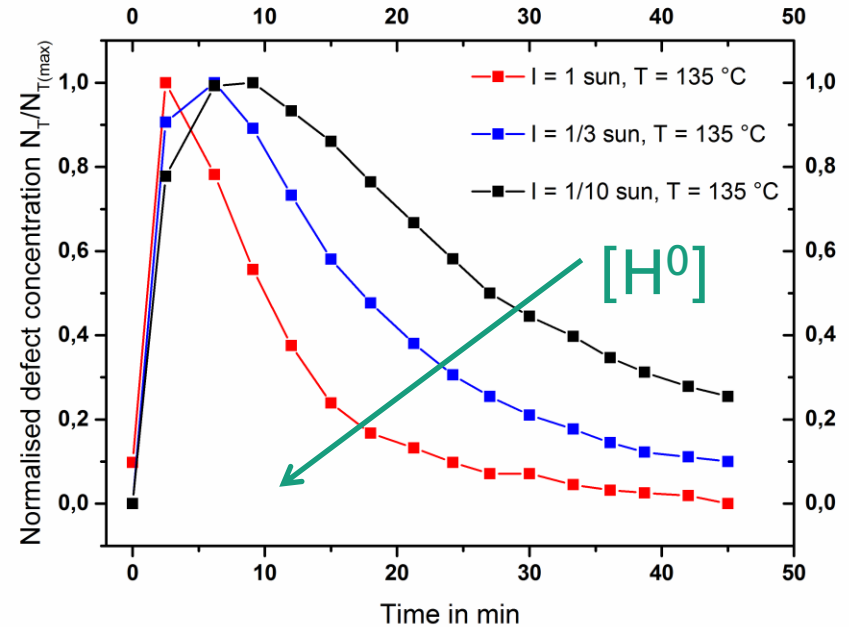
Temperature



Transient degradation-regeneration cycle of neighboured Cz mono Si cells in dependence on temperature

Exponential increase with T:
 $k_i = v_{ch,i} \cdot \exp(-E_{A,i}/kT)$

Intensity



Transient degradation-regeneration cycle of Cz mono Si cell in dependence on light intensity (Data taken from [3])

Linear increase of k_{reg} with $[H^0]$ controlled
 by charge carrier density n, p

Content

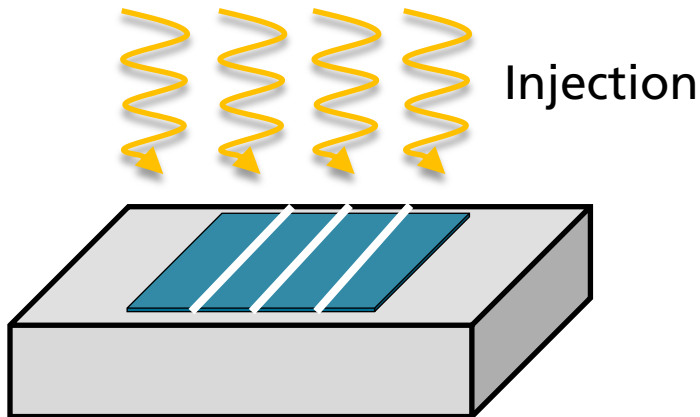
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Current induced regeneration CIR

Comparison of LIR and CIR

Light induced regeneration LIR

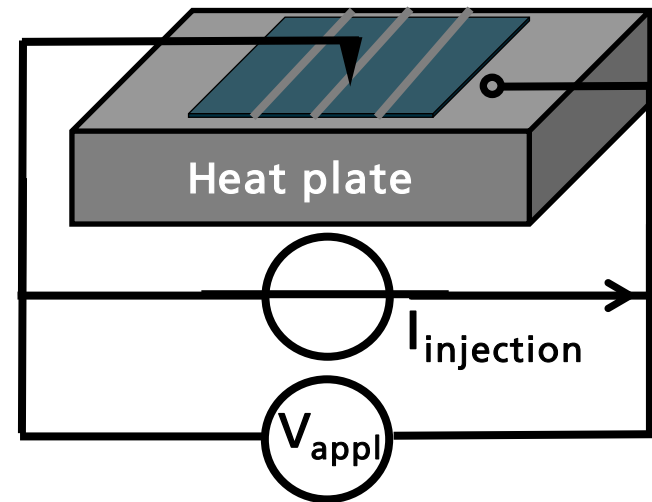
- State of the art for industrial regeneration:



- High illumination (over 100 suns) via laser during or after contact-firing

Current induced regeneration

1. Robust process design
2. No energy transfer losses ($\eta_{\text{Laser}} \sim 30\%$)
3. In situ process control

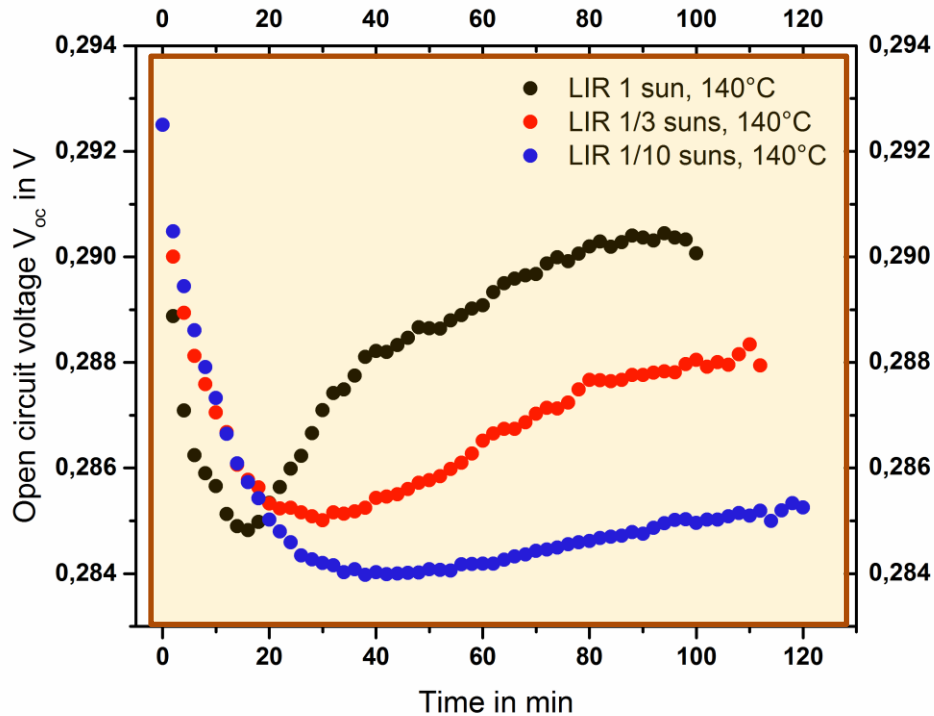


Current induced regeneration CIR

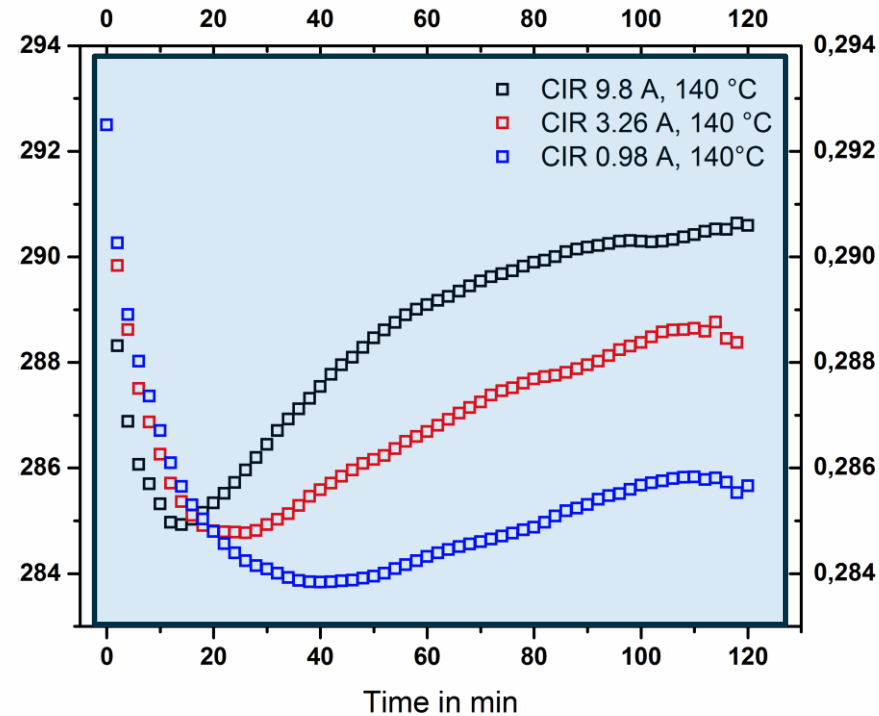
Comparison of LIR and CIR

- light and current induced regeneration using identical solar cells under identical process conditions

LIR

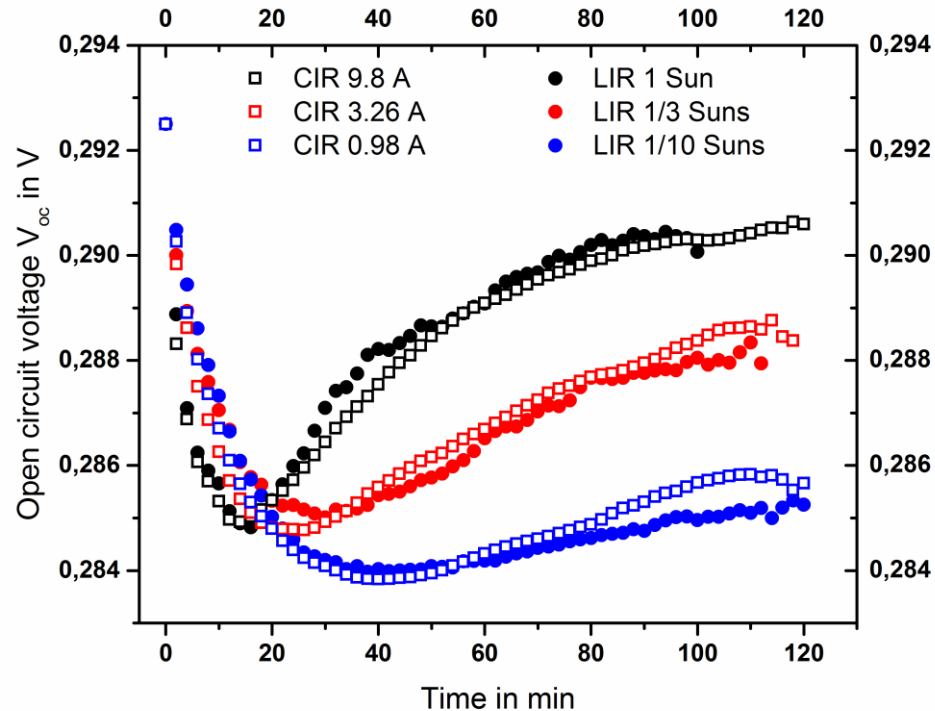


CIR



Current induced regeneration CIR

Comparison of LIR and CIR



- Using same injection conditions $I_{sc} = I_F$
→ same kinetic behaviour
- Proof: Physical mechanism of regeneration based on charge carrier injection!

Electrical regeneration as promising alternative for efficiency stabilization!

Current induced regeneration CIR

Implementing CIR in the value chain

- Forward biasing as an easily convertible approach for charge carrier injection
- Works on series connected cells
- Opens up new process designs and implementation in value chain

CIR on cell level

Advantages:

- i.) easy upscaling through cell stacking
- ii.) usage of medium process parameters

CIR on module level

„Biased lamination“

- i.) usage of lamination process
- ii.) no extra heating step necessary
- iii.) LID free modules independent of solar cell supplier

Content

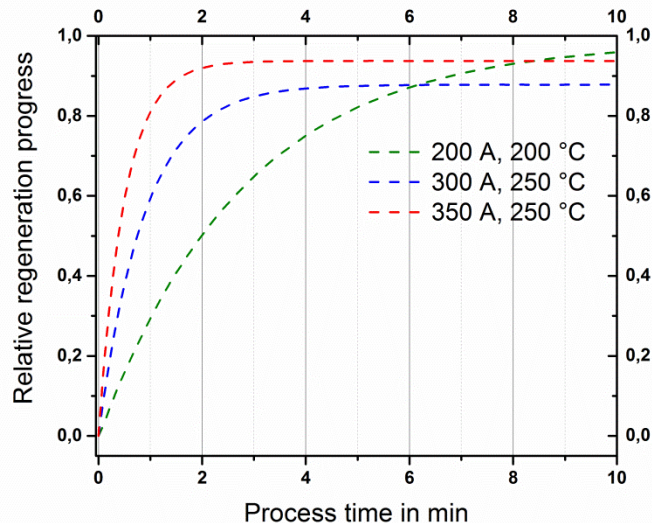
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Application on cell and module level

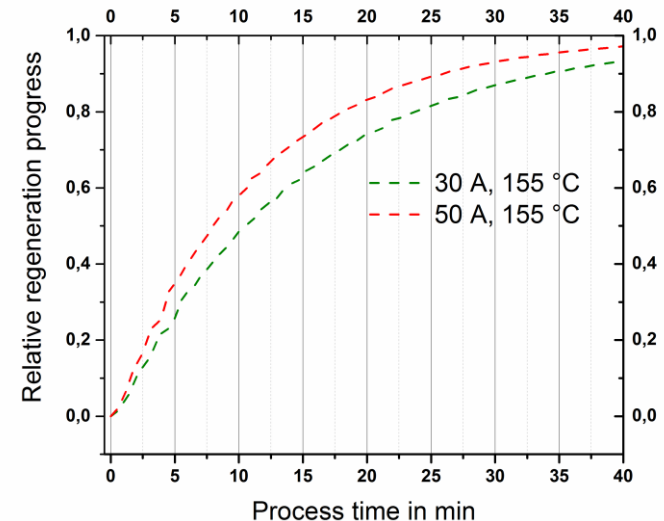
Simulations

- Process parameters for both scenarios differ substantially:
 - Temperature
 - Injection/forward current
 - Time regime
- Preliminary investigation of regeneration gain and process design by applying kinetical model [1]

CIR on cell level



CIR on module level



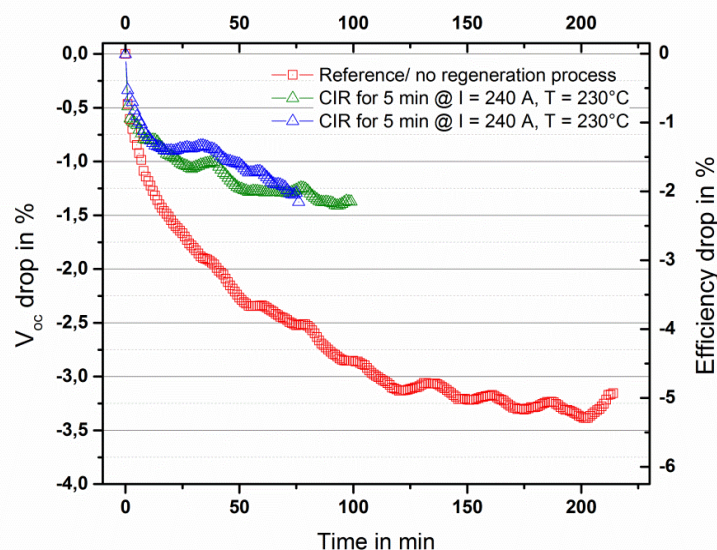
Application of CIR on cell and module level

Proof of concept

- First experimental investigations by applying CIR processes and subsequent light soaking with 1 sun equivalent at 65 °C

CIR on cell level

- Development of regeneration tool
 - Up to $I = 340 \text{ A}$ and $T = 300^\circ\text{C}$
 - In-situ process control via Suns-Voc measurements



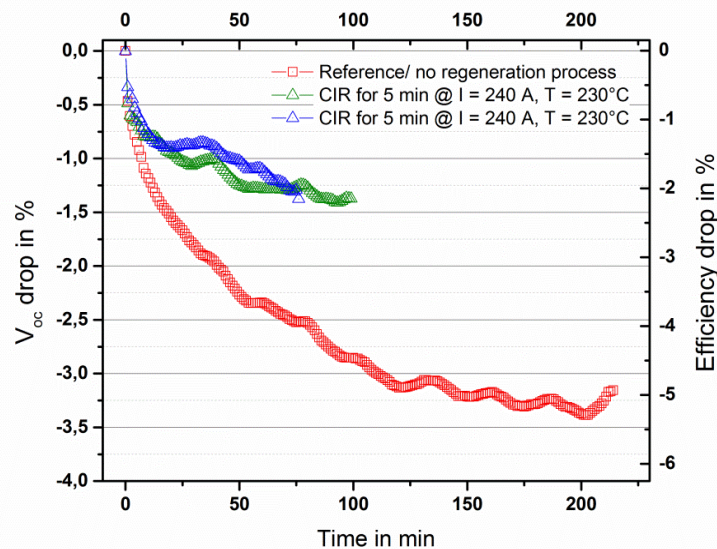
Application on cell and module level

Proof of concept

- First experimental investigations by applying CIR processes and subsequent light soaking with 1 sun equivalent at 65 °C

CIR on cell level

50 % less LID!!!



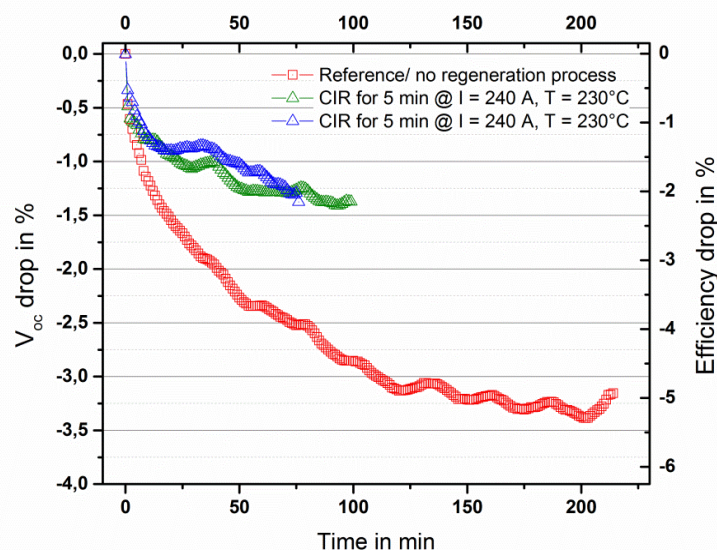
Application on cell and module level

Proof of concept

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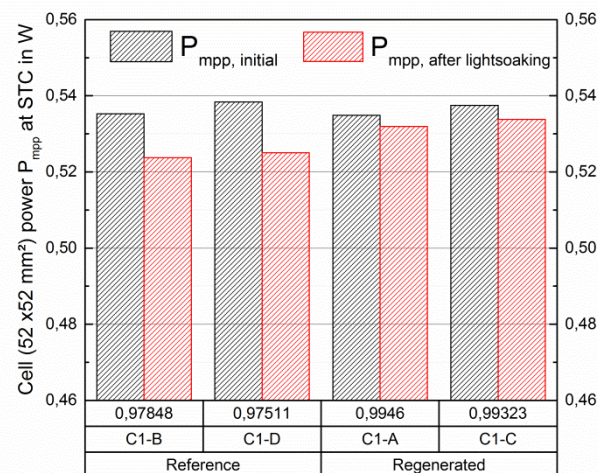
CIR on cell level

50 % less LID!!!



CIR on module level

- Experimental simulation of „biased lamination“ on mini solar cells (52x52 mm²) via LIDScope
- I = 30 A/full cell, T = 155°C, t = 15 min



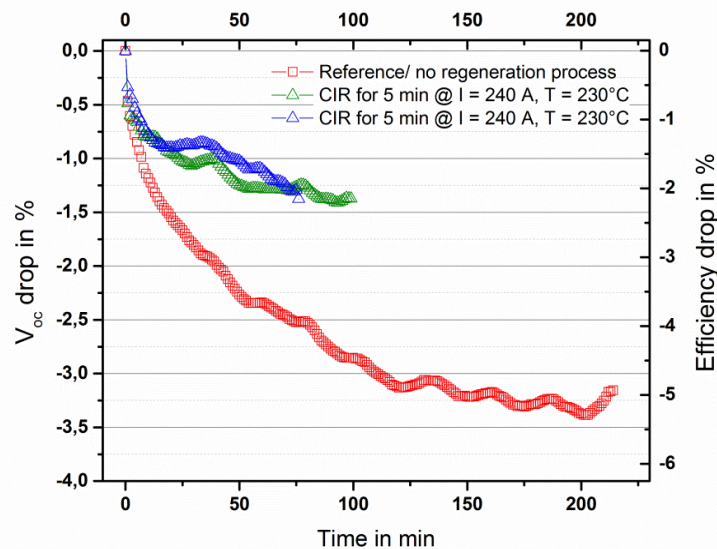
Application on cell and module level

Proof of concept

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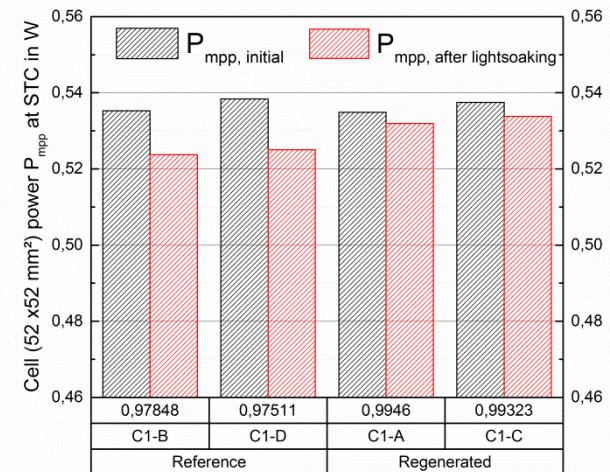
CIR on cell level

50 % less LID!!!



CIR on module level

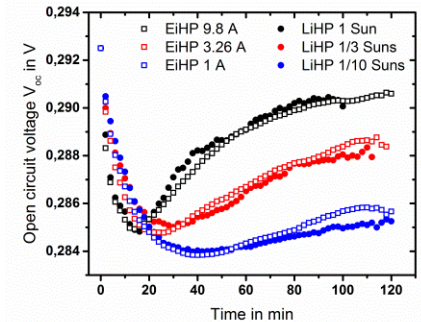
Efficiency gain of 2 %!!!



Summary

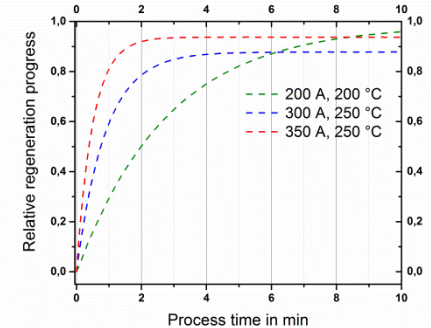
1. Similar kinetic behaviour of LIR and CIR

→ **Current induced regeneration as alternative** for implementation of efficiency stabilization on cell and module level



2. Mathematical description of transient defect concentration

→ Model for preliminary investigations of process design



3. Tools for experimental investigations

→ **Proof of concept of current induced regeneration CIR on cell and module level**

